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              **Image available**
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 Mask defect checking device for electron beam exposure, compares mask
 signal and CAD signal which are generated according to mask shape, to
 check defects of mask
 Patent Assignee: SEIKO INSTR INC (DASE ); MATSUOKA R (MATS-I)
 Inventor: MATSUOKA R
 Number of Countries: 004 Number of Patents: 004
 Patent Family:
 Patent No
               Kind
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✓US 20020024019 A1 20020228 US 2001933785 A
                                                   20010820 200237
                    20020308 JP 2000254970 A
 JP 2002071331 A
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✓DE 10141422 A1 20020508 DE 1041422
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                                                  20010823
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 KR 2002016541 A
                    20020304 KR 200150912
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 Priority Applications (No Type Date): JP 2000254970 A 20000825
 Patent Details:
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                                      Filing Notes
 US 20020024019 A1 8 G21G-005/00
 JP 2002071331 A
                      6 G01B-015/00
 DE 10141422
              A1
                        G01M-011/02
 KR 2002016541 A
                        H01L-021/66
 Abstract (Basic): US 20020024019 A1
         NOVELTY - A sensitivity regulator (5) outputs a mask signal
     according to a mask shape, based on electrons passing through the mask.
     A CAD signal generator (8) outputs a CAD signal showing a required mask
     shape in synchronism with the output of mask signal based on CAD data
     (DT) for making the mask. A signal comparator (6) compares the mask and
     CAD signals, and accordingly checks the defects of mask.
         DETAILED DESCRIPTION - An INDEPENDENT CLAIM is also included for
     mask defect checking method.
         USE - For checking defects of a mask used in electron beam
     exposure, in patterning process of semiconductors.
         ADVANTAGE - Increases speed of defect checking of the electron beam
     exposure mask. Eliminates the need to acquire an optical image of an
     electron beam exposure mask and checks promptly and accurately whether
     or not there are defects in an electron beam exposure mask, using an
     electric signal and a CAD signal based on transmission electrons
     acquired using electron beam scanning.
         DESCRIPTION OF DRAWING(S) - The figure shows a schematic diagram of
     mask defect checking device.
         Sensitivity regulator (5)
         Signal comparator (6)
         CAD signal generator (8)
         pp; 8 DwgNo 1/4
 Title Terms: MASK; DEFECT; CHECK; DEVICE; ELECTRON; BEAM; EXPOSE; COMPARE;
   MASK; SIGNAL; CAD; SIGNAL; GENERATE; ACCORD; MASK; SHAPE; CHECK; DEFECT;
   MASK
 Derwent Class: P34; S02; S03; U11
 International Patent Class (Main): G01B-015/00; G01M-011/02; G21G-005/00;
   H01L-021/66
 International Patent Class (Additional): A61N-005/00; G01B-015/04;
   G01M-019/00; G01N-023/04; G03F-001/08; G03F-007/20; H01J-037/00;
   H01L-021/027
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File Segment: EPI; EngPI